

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Not for submission under 37 CFR 1.99)

Application Number	10/586,543
Confirmation Number	6159
Filing Date	July 19, 2006
First Named Inventor	Yasuhito URASHIMA
Art Unit	2826
Examiner Name	AHMED, SELIM U
Attorney Docket Number	Q79654

U.S. PATENTS

Examiner Initials*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

U.S. PATENT APPLICATION PUBLICATIONS

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FOREIGN PATENT DOCUMENTS

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NON-PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	T ⁵
	1.	Takahiro ITO, et al.; "Influence of Thermal Annealing on GaN Buffer Layers and the Property of Subsequent GaN Layers Grown by Metalorganic Chemical Vapor Deposition"; Jpn. J. Appl. Phys., Part 1, Vol. 38, No. 2A; February 1999; pp. 649-653; XP-002616994	
	2.	Shigekazu SANO, et al.; "Low-dislocation-density GaN and $\text{G}_{1-x}\text{Al}_x\text{N}$ ($x \leq 0.13$) grown on grooved substrates; Journal of Crystal Growth; Vol. 234, No. 1-4; 1 February 2002; pp. 129-134; XP 004333449	
	3.	A. Kakanakova-Georgieva, et al.; "Epitaxial Growth of AlN Layers on SiC Substrates in a Hot-Wall MOCVD System"; phys. stat. sol. (c) Vol. 0; No. 1; 2002; pp. 205-208; XP-002616996	
	4.	J.A. POWELL, et al.; "Process-Induced Morphological Defects in Epitaxial CVD Silicon Carbide"; phys. stat. sol. (b); Vol. 202, No. 1; 1 July 1997; pp. 529-548; XP-002616995	

EXAMINER SIGNATURE

Examiner Signature	Date Considered
/Selim Ahmed/	03/03/2011

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CERTIFICATION STATEMENT

Please see 37 CFR 1.97 and 1.98 to make the appropriate selection(s):

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OR

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- ☒ That each item of information contained in the Information Disclosure Statement filed concurrently herewith was first cited in any communication from a foreign patent office in a counterpart foreign application, and that the communication was not received by any individual designated in 37 C.F.R. § 1.56(c) more than thirty days prior to the filing of said Information Disclosure Statement. See 37 CFR 1.704(d).

- ☒ Fee set forth in 37 CFR 1.17 (p) has been submitted herewith.

- ☒ The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

- ☐ None


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A signature of the applicant or representative is required in accordance with CFR 1.33, 10.18. Please see CFR 1.4(d) for the form of the signature.

Signature		Date (YYYY-MM-DD)	2011-02-28
Name/Print	Abraham J. Rosner	Registration Number	33,276

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